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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet of 1

Complete if Known								
Application Number	10/627,218							
Filing Date	July 25, 2003							
First Named Inventor	Yeo, et al.							
Art Unit	2831							
Examiner Name	На							
Attorney Docket Number	TSM03-0556							

			U.S. PATE	NT DOCUMENTS	
Examiner trilials*	Cite No.	Document Number Number - Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Cotumns, Lines, Where Relevant Passages or Relevant Figures Appear
17	7	US- 2004/0026765 A1	02-12-2004	Currie, et al.	

		FOREIG	N PATENT DOC	JMENTS		
Examiner tritials*		Foreign Patent Document	0.45	Name of Patentee or	Pages, Columns, Lines,	Т
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Sheet 5

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Attorney Docket Number	TSM03-0556						

	U.S. PATENT DOCUMENTS									
Examiner Initials*	Cite No.1	Document Number Number - Kind Code ² (if knawn)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear					
NH	1	US-4,314,269	02-02-1982	Fujiki						
	2	US-4,631,803	12-30-1986	Hunter, et al.						
	3	US-4,946,799	08-07-1990	Blake, et al.						
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Subs	titute for form 1449	3/PTO		Application Number	10/627,218	
10.000				Filing Date	July 25, 2003	
	ORMATION			First Named Inventor	Yeo, et al.	
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Sheet	2	of	5	Attorney Docket Number	TSM03-0556	

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nitials*	No.1	Number - Kind Code ² (if known)	MM-DD-YYYY	Applicant of Cited Document		
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	24	US-6,448,114 B1	09-10-2002	An, et al.		
	25	US-6,489,664 B2	12-03-2002	Re, et al.		
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141	31	US-6,653,700 B2	11-25-2003	Chau, et al.		
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Substitu	ute for form 1449	В/РТО		Complete if Known			
				Application Number	10/627,218		
11	NFORMATIO	N DISCLO	SURE	Filing Date	July 25, 2003		
	TATEMENT			First Named Inventor	Yeo, et al.		
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				Examiner Name	TBD		
Sheet	. 3	of	5	Attorney Docket Number	TSM03-0556		

		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (bock, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	72
NH	32	ISMAIL, K, et al., "Electron Transport Properties of Si/SiGe Heterostructures: Measurements and Device Implications," Applied Physics Letters, Vol. 63, No. 5, (August 2, 1993), pp. 660-662.	
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Substitute for form 1449B/PTO Complete if Known Application Number 10/627,218 **INFORMATION DISCLOSURE** Filing Date July 25, 2003 First Named Inventor Yeo, et al. STATEMENT BY APPLICANT Group Art Unit (use as many sheets as necessary) 2831 Examiner Name TBD Sheet of Attorney Docket Number TSM03-0556

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		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS						
Examiner	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the							
Initiats*	No.	item (book, magazine, journal, sarial, symposium, catalog, etc.), date, page(s), volume-issue	T ²					
		number(s), publisher, city end/or country where published.						
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				Examiner Name	TBD	
Sheet	5	of	5	Attomey Docket Number	TSM03-0556	

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